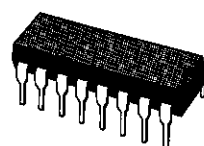
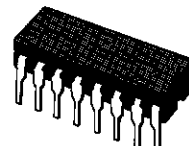


DUAL 64-STAGE STATIC SHIFT REGISTER

- CLOCK FREQUENCY 12MHz (TYP.) AT $V_{DD} = 10V$
- SCHMITT TRIGGER CLOCK INPUTS ALLOW OPERATION WITH VERY SLOW CLOCK RISE AND FALL TIMES
- THREE-STATE OUTPUTS
- QUIESCENT CURRENT SPECIFIED AT 20V FOR HCC DEVICE
- STANDARDIZED, SYMMETRICAL OUTPUT CHARACTERISTICS
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N°. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"



EY
(Plastic Package)



F
(Ceramic Package)



C1
(Chip Carrier)

ORDER CODES :

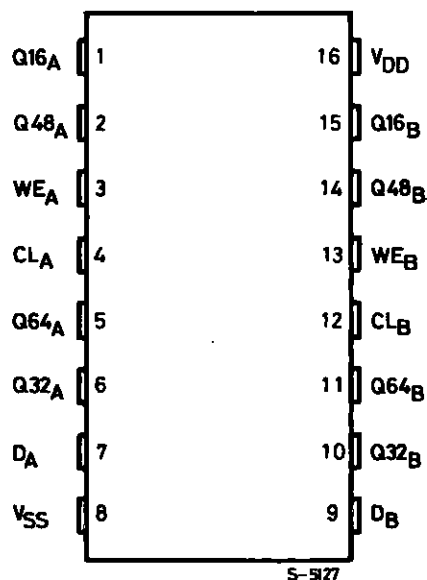
HCC4517BF HCF4517BM1
HCF4517BC1

DESCRIPTION

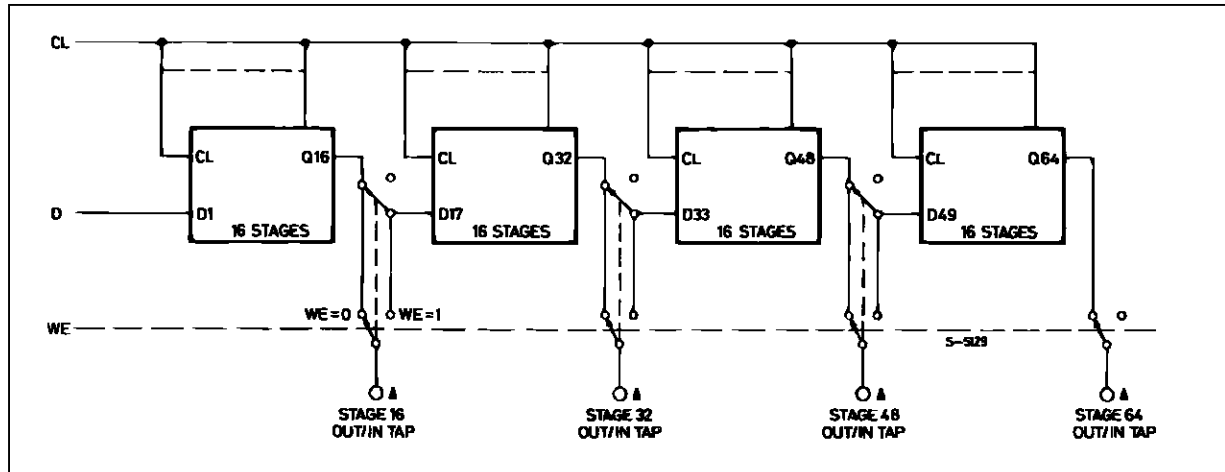
The **HCC4517B** (extended temperature range) and **HCF4517B** (intermediate temperature range) are monolithic integrated circuits, available in 16-lead dual in-line plastic or ceramic package.

The **HCC/HCF4517B** dual 64-stage static shift register consists of two independent registers each having a clock, data, and write enable input and outputs accessible at taps following the 16th, 32nd, 48th, and 64th stages. These taps also serve as input points allowing data to be inputted at the 17th, 33rd, and 49th stages when the write enable input is a logic 1 and the clock goes through a low-to-high transition. The truth table indicates how the clock and write enable inputs control the operation of the **HCC/HCF4517B**. Inputs at the intermediate taps allow entry of 64 bits into the register with 16 clock pulses. The 3-state outputs permit connection of this device to an external bus.

PIN CONNECTIONS



FUNCTIONAL DIAGRAM (one half)



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DD}^*	Supply Voltage : HCC Types HCF Types	– 0.5 to + 20 – 0.5 to + 18	V V
V_i	Input Voltage	– 0.5 to $V_{DD} + 0.5$	V
I_i	DC Input Current (any one input)	± 10	mA
P_{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T_{op} = Full Package-temperature Range	200 100	mW mW
T_{op}	Operating Temperature : HCC Types HCF Types	– 55 to + 125 – 40 to + 85	°C °C
T_{stg}	Storage Temperature	– 65 to + 150	°C

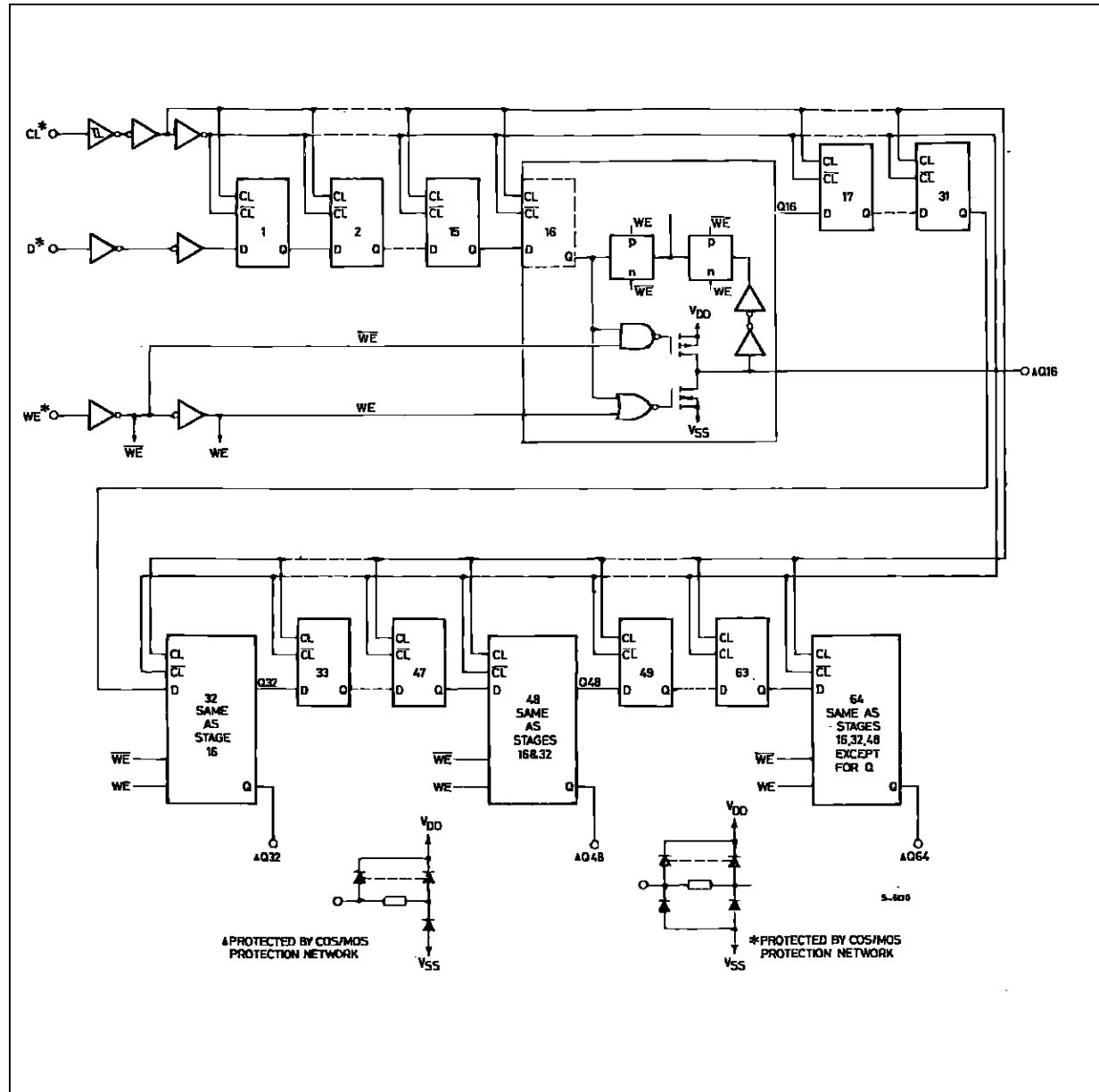
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

* All voltages are with respect to V_{SS} (GND).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage : HCC Types HCF Types	3 to 18 3 to 15	V V
V_i	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature : HCC Types HCF Types	– 55 to + 125 – 40 to + 85	°C °C

LOGIC DIAGRAM AND TRUTH TABLE



Clock	Write Enable	Data	Stage 16 Tap	Stage 32 Tap	Stage 48 Tap	Stage 64 Tap
0	0	X	Q16	Q32	Q48	Q64
0	1	X	Z	Z	Z	Z
1	0	X	Q16	Q32	Q48	Q64
1	1	X	Z	Z	Z	Z
$\downarrow$	0	DI In	Q16	Q32	Q48	Q64
$\downarrow$	1	Di In	D17 In	D33 In	D49 In	Z
$\downarrow$	0	X	Q16	Q32	Q48	Q64
$\downarrow$	1	X	Z	Z	Z	Z

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μA)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/ 5			5		5		0.04	5		150	μA
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
			0/20			20		100		0.08	100		3000	
		HCF Types	0/ 5			5		20		0.04	20		150	
			0/10			10		40		0.04	40		300	
			0/15			15		80		0.04	80		600	
V _{OH}	Output High Voltage	0/ 5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/ 5	2.5		5	− 2		− 1.6	− 3.2		− 1.15		mA
			0/ 5	4.6		5	− 0.64		− 0.51	− 1		− 0.36		
			0/10	9.5		10	− 1.6		− 1.3	− 2.6		− 0.9		
			0/15	13.5		15	− 4.2		− 3.4	− 6.8		− 2.4		
		HCF Types	0/ 5	2.5		5	− 1.53		− 1.36	− 3.2		− 1.1		
			0/ 5	4.6		5	− 0.52		− 0.44	− 1		− 0.36		
			0/10	9.5		10	− 1.3		− 1.1	− 2.6		− 0.9		
			0/15	13.5		15	− 3.6		− 3.0	− 6.8		− 2.4		
I _{OL}	Output Sink Current	HCC Types	0/ 5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/ 5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input	18		± 0.1		±10 ^{−5}	± 0.1		± 1	μA	
		HCF Types	0/15		15		± 0.3		±10 ^{−5}	± 0.3		± 1		
I _{OH} , I _{OL}	3-State Output Leakage Current	HCC Types	0/18		18		± 0.4		±10 ^{−4}	± 0.4		± 12	μA	
		HCF Types	0/18		15		± 1.0		±10 ^{−4}	± 1.0		± 7.5		
C _I	Input Capacitance			Any Input					5	7.5			pF	

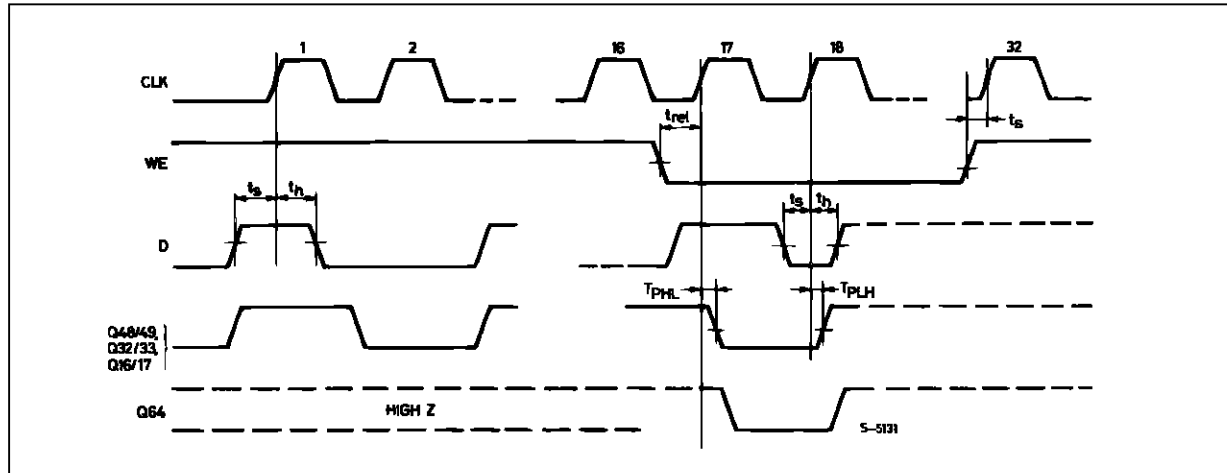
* T_{Low} = - 55°C for **HCC** device : - 40°C for **HCF** device.* T_{High} = + 125°C for **HCC** device : + 85°C for **HCF** device.The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V,

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, Input $t_r, t_f = 20\text{ns}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$)

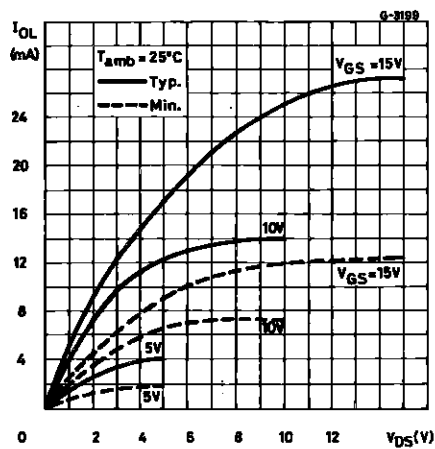
Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PHL}, t_{PLH}	Propagation Delay Time : CL to Bit 16 Tap		5		200	400	ns
			10		110	220	
			15		90	180	
t_{PLZ}, t_{PHZ} t_{PZL}, t_{PZH}	3-State Output WE to Bit 16 Tap (see note)		5		75	150	ns
			10		40	80	
			15		30	60	
t_{THL}, t_{TLH}	Output Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	
t_{setup}	Write Enable to Clock		5	- 100	- 50		ns
			10	- 50	- 25		
			15	- 30	- 15		
t_{setup}	Data to Clock		5	- 100	- 50		ns
			10	- 60	- 30		
			15	- 30	- 15		
	Write Enable to Clock Release Time		5		50	100	ns
			10		25	50	
			15		20	40	
t_{hold}	Data to Clock		5		100	200	ns
			10		50	100	
			15		25	50	
t_w	Minimum Clock Pulse Width		5		90	180	ns
			10		40	80	
			15		25	50	
f_{CL}	Maximum Clock Input Frequency		5	3	6		MHz
			10	6	12		
			15	8	15		
t_r, t_f	Maximum Clock Input Rise or Fall Time		5	UNLIMITED			μs
			10				
			15				

Note : Measured at the point of 10% change in output load of 50pF, $R_L = 1\text{k}\Omega$ to V_{DD} for t_{PZL} , t_{PLZ} and $R_L = 1\text{k}\Omega$ to V_{SS} for t_{PHZ} .

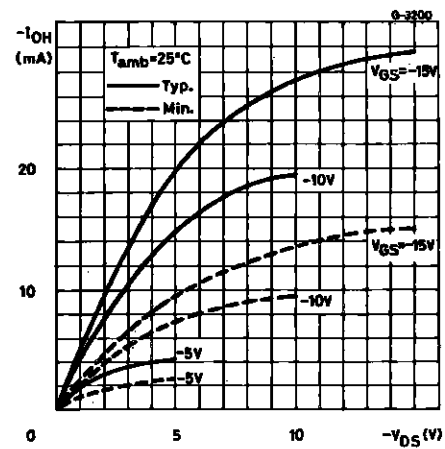
WAVEFORMS



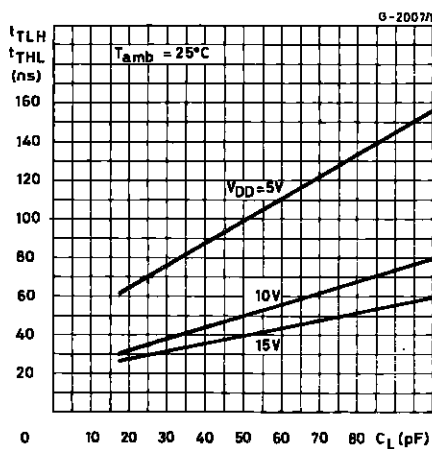
Output Low (sink) Current Characteristics.



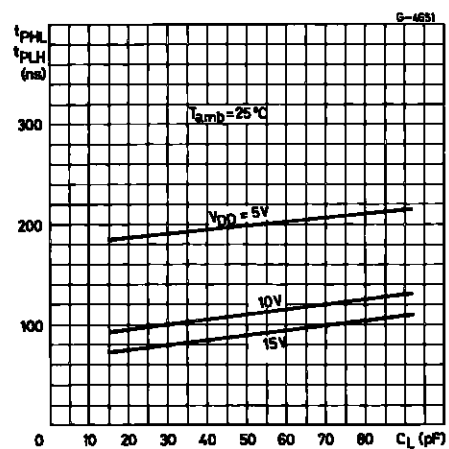
Output High (source) Current Characteristics.



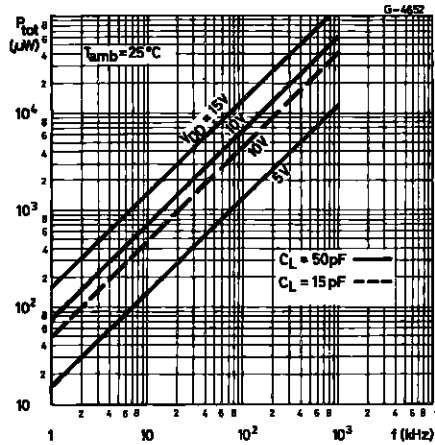
Typical Transition Time vs. Load Capacitance.



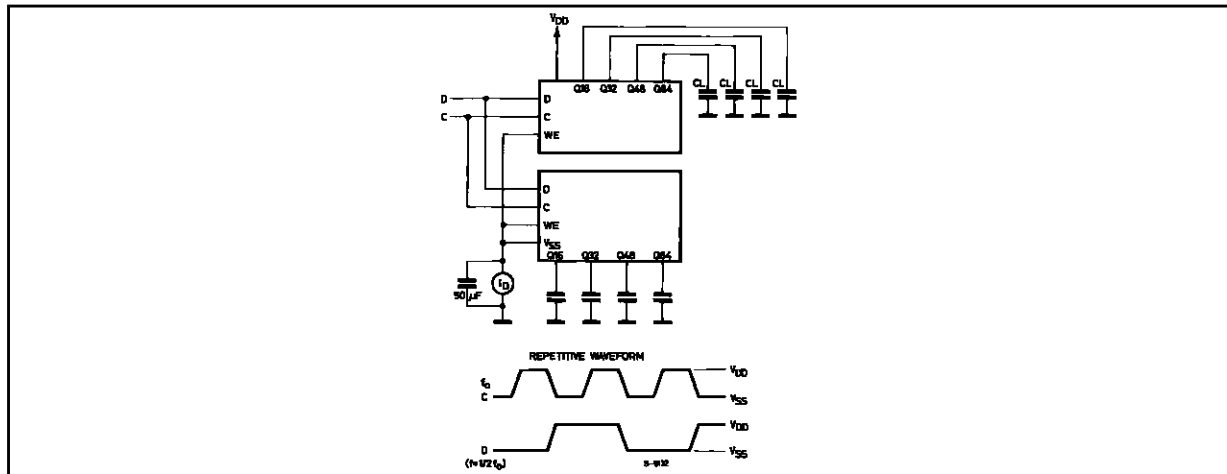
Typical Propagation Delay Time vs. Load Capacitance.



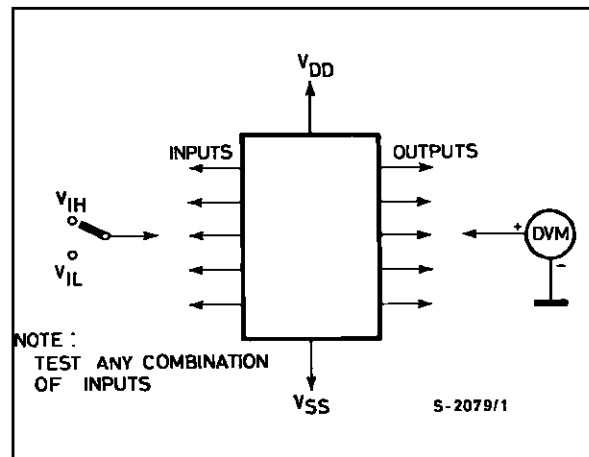
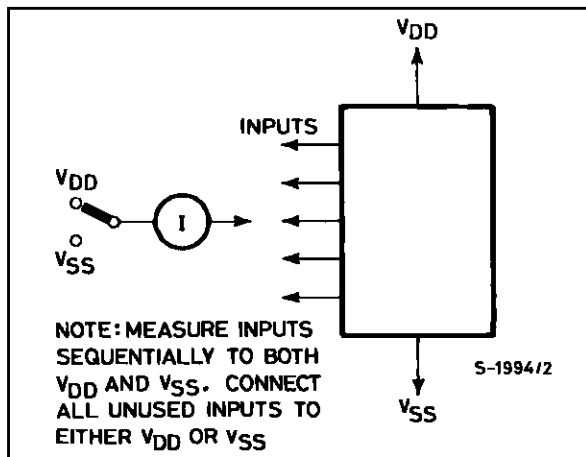
Typical Dynamic Power Dissipation vs. Frequency.



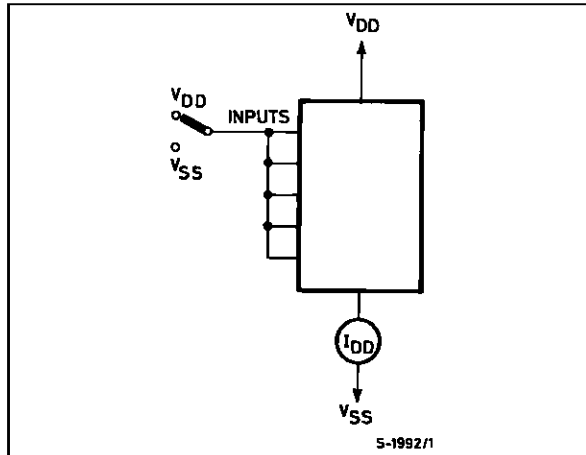
Dynamic Power Dissipation and Waveforms.



TEST CIRCUITS

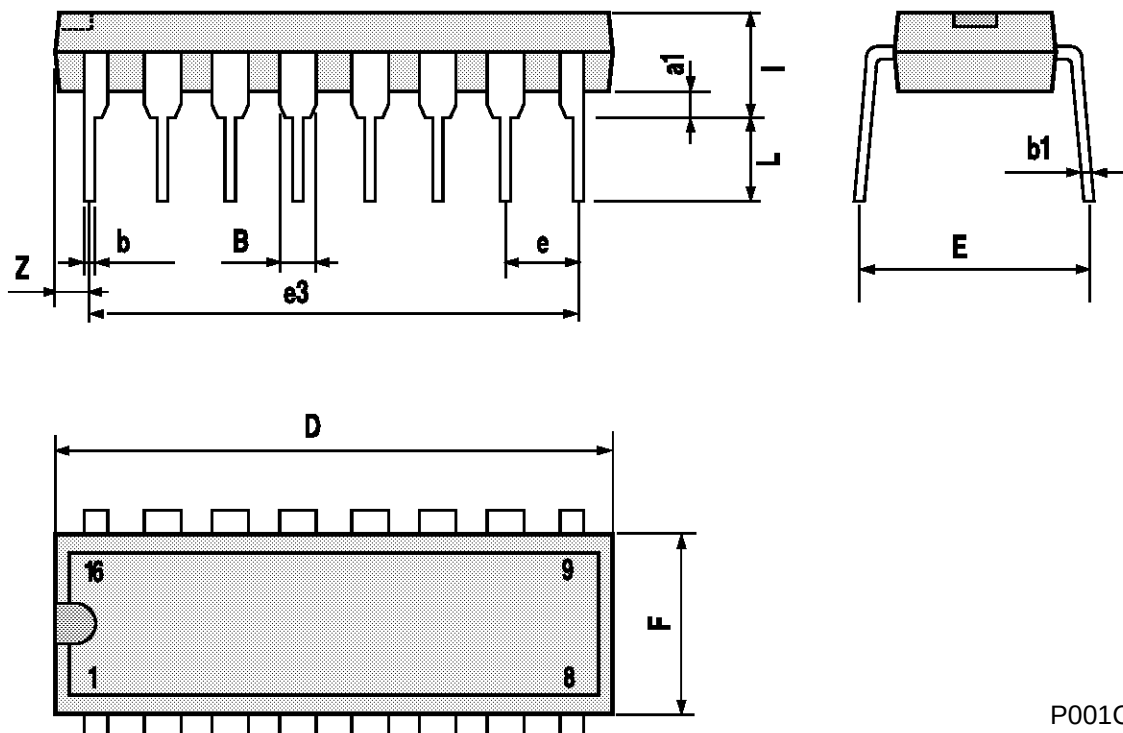


TEST CIRCUITS (continued)



Plastic DIP16 (0.25) MECHANICAL DATA

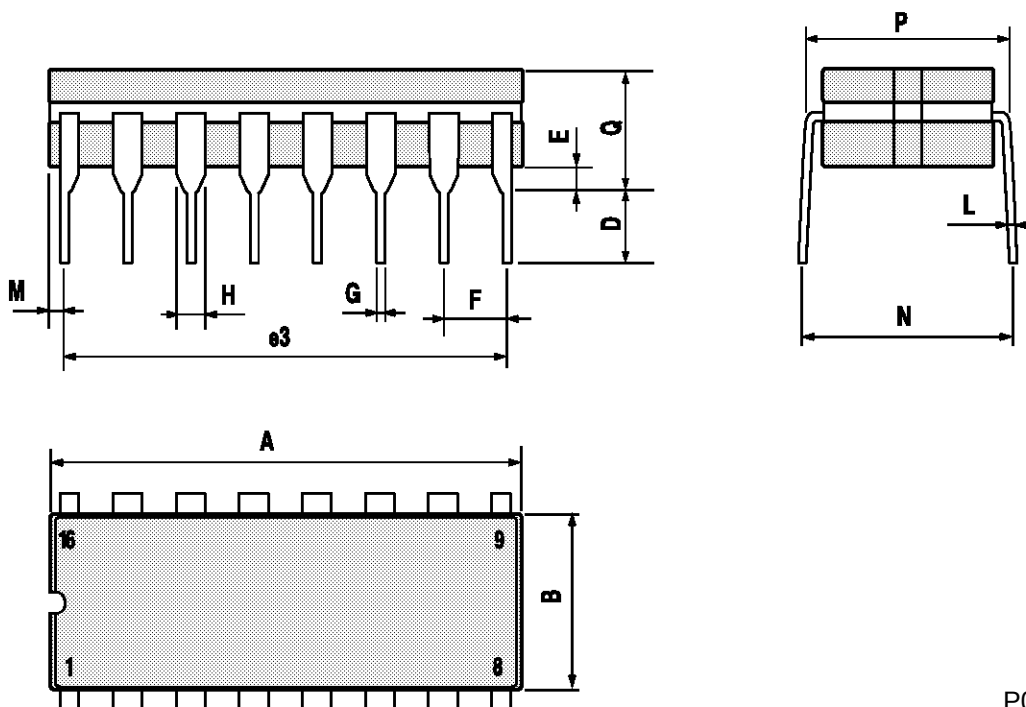
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	0.77		1.65	0.030		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		17.78			0.700	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z			1.27			0.050



P001C

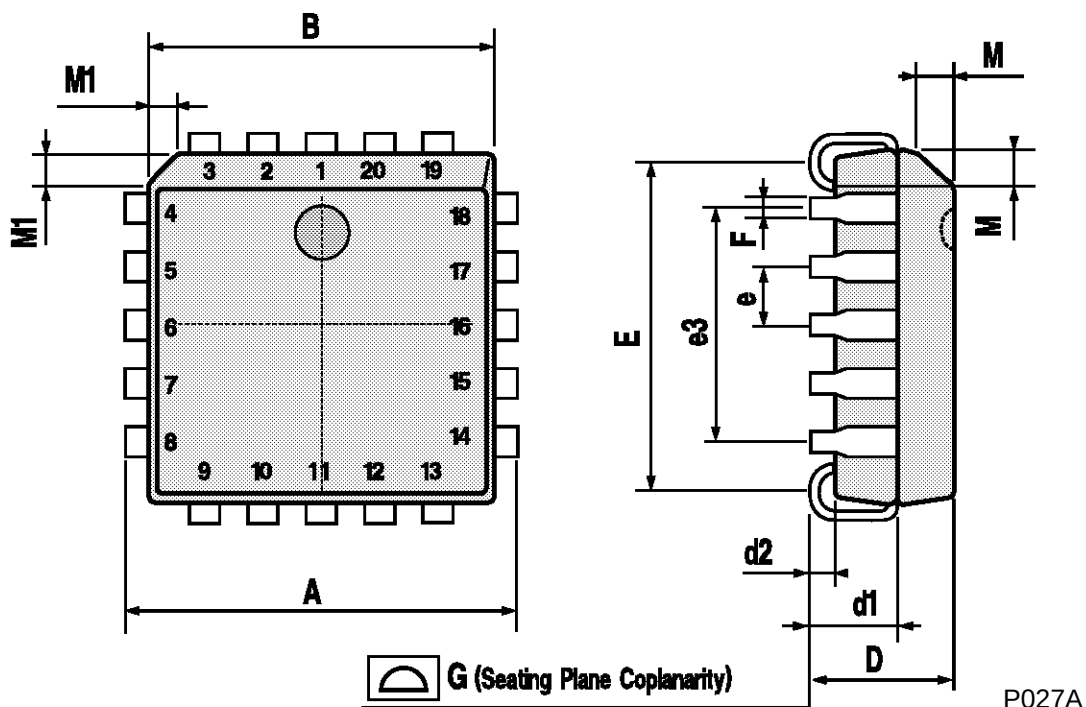
Ceramic DIP16/1 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			20			0.787
B			7			0.276
D		3.3			0.130	
E	0.38			0.015		
e3		17.78			0.700	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
H	1.17		1.52	0.046		0.060
L	0.22		0.31	0.009		0.012
M	0.51		1.27	0.020		0.050
N			10.3			0.406
P	7.8		8.05	0.307		0.317
Q			5.08			0.200



PLCC20 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	9.78		10.03	0.385		0.395
B	8.89		9.04	0.350		0.356
D	4.2		4.57	0.165		0.180
d1		2.54			0.100	
d2		0.56			0.022	
E	7.37		8.38	0.290		0.330
e		1.27			0.050	
e3		5.08			0.200	
F		0.38			0.015	
G			0.101			0.004
M		1.27			0.050	
M1		1.14			0.045	



Information furnished is believed to be accurate and reliable. However, SGS-THOMSON Microelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of SGS-THOMSON Microelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. SGS-THOMSON Microelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of SGS-THOMSON Microelectronics.

© 1994 SGS-THOMSON Microelectronics - All Rights Reserved

SGS-THOMSON Microelectronics GROUP OF COMPANIES

Australia - Brazil - France - Germany - Hong Kong - Italy - Japan - Korea - Malaysia - Malta - Morocco - The Netherlands -
Singapore - Spain - Sweden - Switzerland - Taiwan - Thailand - United Kingdom - U.S.A